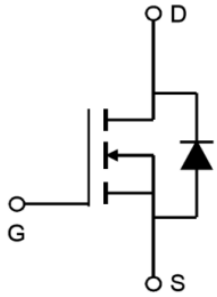
AP2300B-SI-2

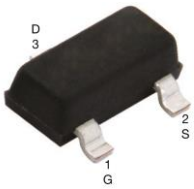
30V N-Channel Enhancement Mode MOSFET

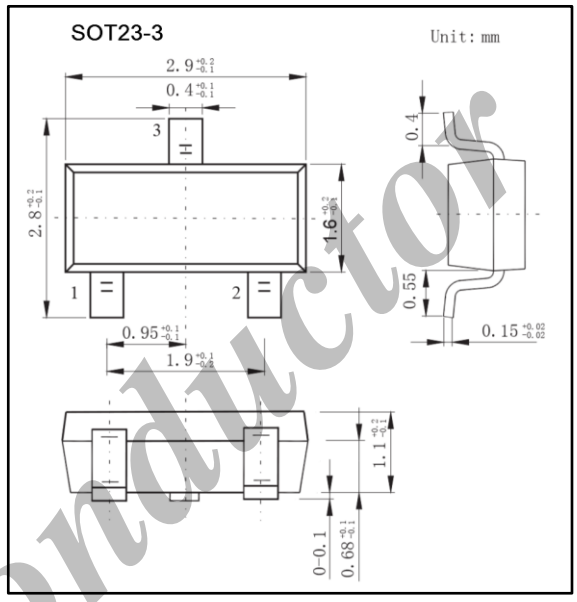
• General Description

AP2300B-SI-2 combines advanced MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is most suitable to load-switch or PWM applications.



Top View





• Applications

- DC/DC converter for portable devices
- Load switch

• Product Summary

V_{DS}	30V
I_D (at V_{GS} = 4.5V)	3.8A
$R_{DS(ON)}$ (at V_{GS} = 10V)	< 55mΩ
$R_{DS(ON)}$ (at V_{GS} = 4.5V)	< 65mΩ
$R_{DS(ON)}$ (at V_{GS} = 2.5V)	< 85mΩ

• Absolute Maximum Ratings Ta = 25℃

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current	T_A=25℃	I_D	3.8	A
	T_A=70℃		3.1	
Pulsed Drain Current *		I_{DM}	15	
Power Dissipation	T_A=25℃	P_D	1.4	W
	T_A=70℃		0.9	
Thermal Resistance. Junction- to-Ambient	t ≤ 10s	$R_{\theta JA}$	90	℃/W
	Steady-State		125	
Thermal Resistance. Junction- to-Lead		$R_{\theta JL}$	80	℃/W
Junction and Storage Temperature Range		T_J , T_{STG}	-55 to 150	℃

* Repetitive rating, pulse width limited by junction temperature.

- **Electrical Characteristics Ta = 25°C**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	I_D=250μA, V_{GS}=0V	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	μA
		V_{DS}=30V, V_{GS}=0V, T_J=55°C			5	
Gate-Body Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±12V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	0.5		1.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=3.8A			55	mΩ
		V_{GS}=10V, I_D=3.8A, T_J=125°C			84	
		V_{GS}=4.5V, I_D=3.5A			65	mΩ
		V_{GS}=2.5V, I_D=1A			85	mΩ
On state Drain Current	$I_{D(ON)}$	V_{GS}=10V, V_{DS}=5V	15			A
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=3.8A		14		S
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=15V, f=1MHz	185	235	285	pF
Output Capacitance	C_{oss}		25	35	45	pF
Reverse Transfer Capacitance	C_{rss}		10	17.5	25	pF
Gate Resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz	2.1		6.5	Ω
Total Gate Charge (10V)	Q_g	V_{GS}=10V, V_{DS}=15V, I_D=3.8A		10	12	nC
Total Gate Charge (4.5V)				4.7		
Gate Source Charge	Q_{gs}			0.95		
Gate Drain Charge	Q_{gd}			1.6		
Turn-On Delay Time	$t_{D(on)}$	V_{GS}=10V, V_{DS}=15V, R_L=3.95Ω, R_{GEN}=3Ω		3.5		ns
Turn-On Rise Time	t_r			1.5		
Turn-Off Delay Time	$t_{D(off)}$			17.5		
Turn-Off Fall Time	t_f			2.5		
Body Diode Reverse Recovery Time	t_{rr}	I_F=3.8A, d_I/d_t=100A/ μs		8.5	11	ns
Body Diode Reverse Recovery Charge	Q_{rr}			2.6	3.5	nC
Maximum Body-Diode Continuous Current	I_S				1.5	A
Diode Forward Voltage	V_{SD}	I_S=1A, V_{GS}=0V			1	V

- **Ordering Information**

Ordering Part Number	Package	MOQ
AP2300B-SI-2	SOT23-3	3,000 pcs / reel

- **Typical Characteristics**

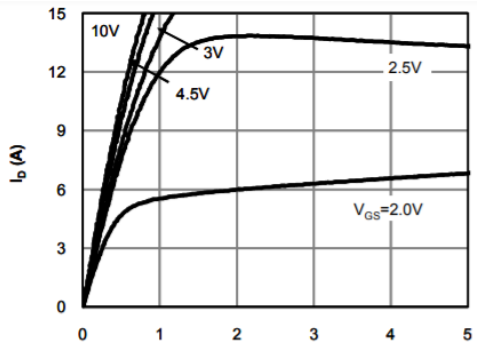


Fig 1: On-Region Characteristics

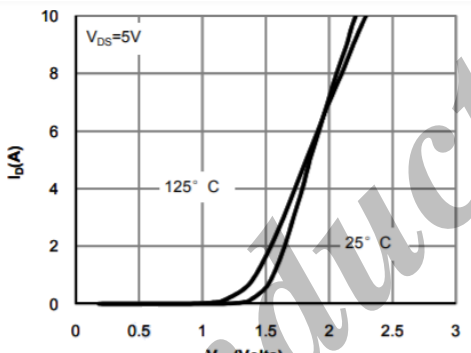


Figure 2: Transfer Characteristics

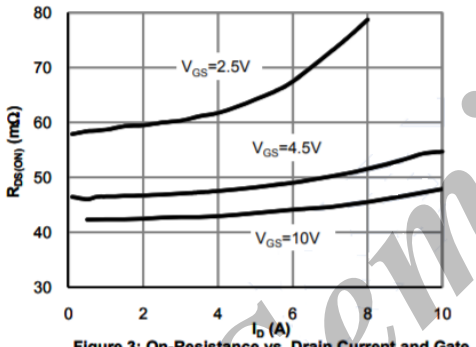


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

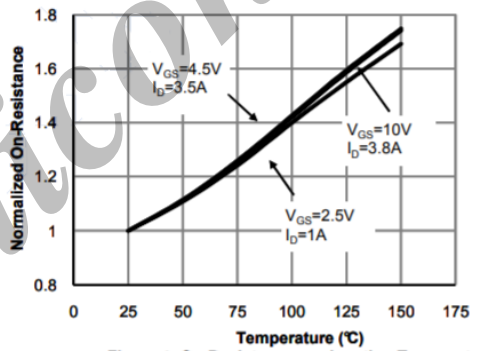


Figure 4: On-Resistance vs. Junction Temperature

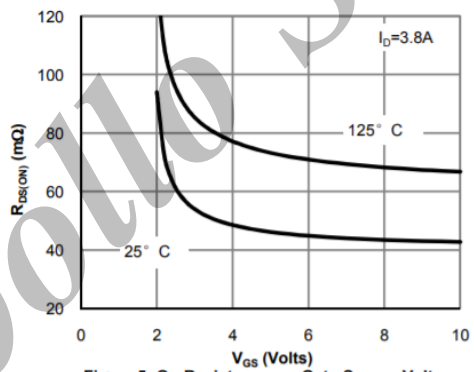


Figure 5: On-Resistance vs. Gate-Source Voltage

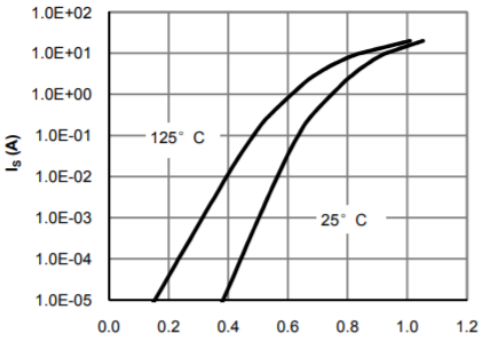


Figure 6: Body-Diode Characteristics

- **Typical Characteristics**

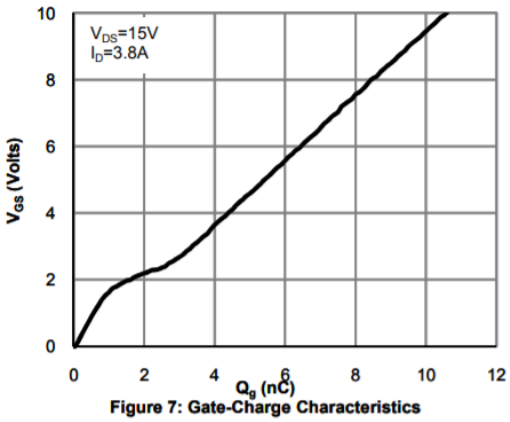


Figure 7: Gate-Charge Characteristics

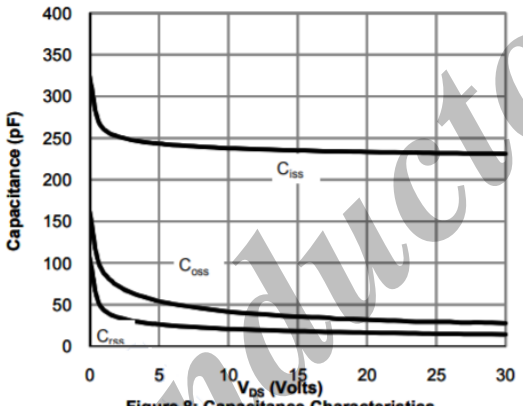


Figure 8: Capacitance Characteristics

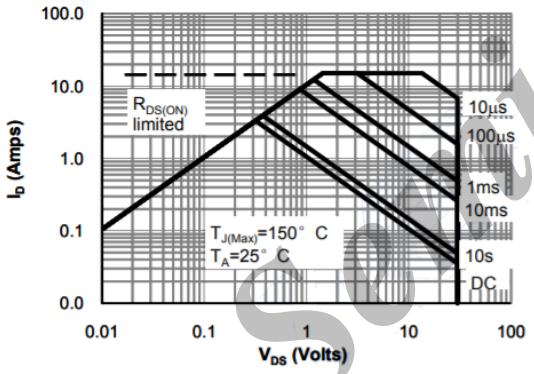


Figure 9: Maximum Forward Biased Safe Operating Area

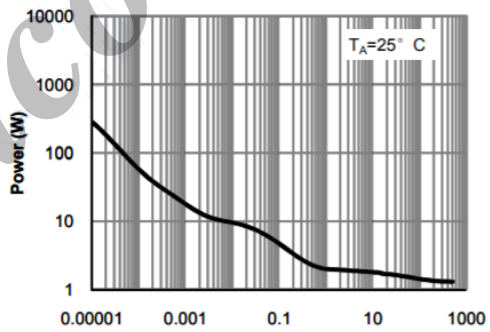


Figure 10: Single Pulse Power Rating Junction-to-Ambient

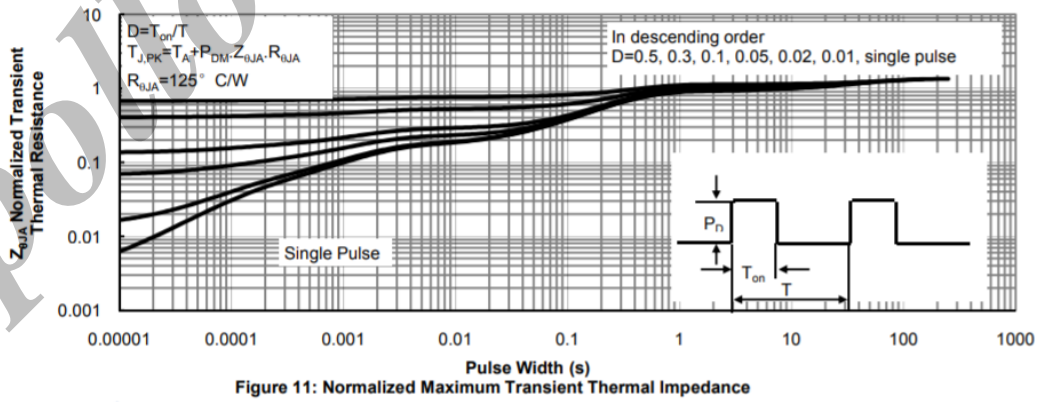


Figure 11: Normalized Maximum Transient Thermal Impedance

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Apollo Semiconductor Ltd., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Apollo"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Apollo makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Apollo disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Apollo's knowledge of typical requirements that are often placed on Apollo products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Apollo's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Apollo products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Apollo product could result in personal injury or death. Customers using or selling Apollo products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Apollo personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Apollo. Product names and markings noted herein may be trademarks of their respective owners